# 2SC4420

## Silicon NPN triple diffusion planar type

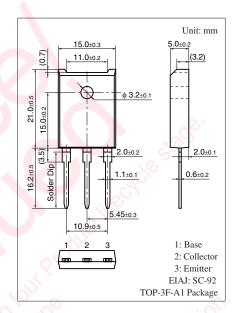
For high breakdown voltage high-speed switching

#### ■ Features

- High-speed switching
- ullet High collector-base voltage (Emitter open)  $V_{CBO}$
- Wide safe operation area
- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	900	V
Collector-emitter voltage (E-B short)	V <sub>CES</sub>	900	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	800	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Base current	$I_{B}$	1	A
Collector current	$I_{C}$	3	A
Peak collector current	$I_{CP}$	5	A
Collector power dissipation	P <sub>C</sub>	70	W
$T_a = 25^{\circ}C$		3.0	5 , 6
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

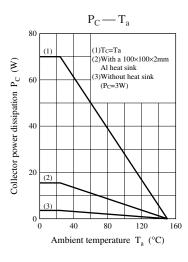


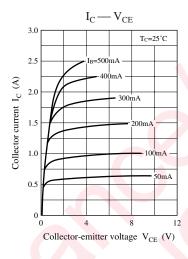
## ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

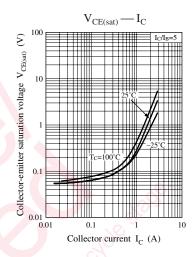
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	800			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 900 \text{ V}, I_{E} = 0$			50	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 7 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ A}$	8			_
	h <sub>FE2</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 0.8 \text{ A}$	6			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 0.8 \text{ A}, I_B = 0.16 \text{ A}$			1.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 0.8 \text{ A}, I_B = 0.16 \text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}, I_{C} = 0.15 \text{ A}, f = 1 \text{ MHz}$		10		MHz
Turn-on time	t <sub>on</sub>	$I_{\rm C} = 0.8 \text{ A}$			0.7	μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.16 \text{ A}, I_{B2} = -0.32 \text{ A}$			2.5	μs
Fall time	$t_{\rm f}$	$V_{CC} = 250 \text{ V}$			0.3	μs

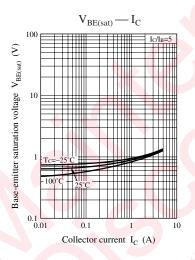
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

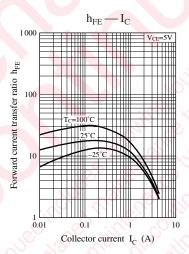
## **Panasonic**

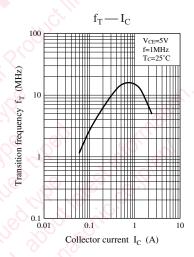


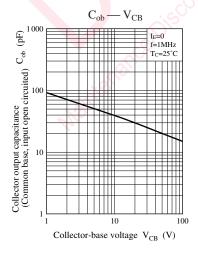


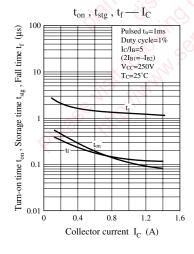


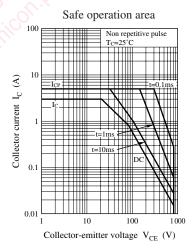






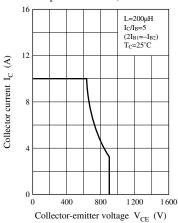




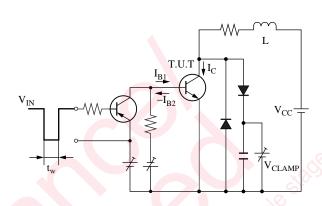


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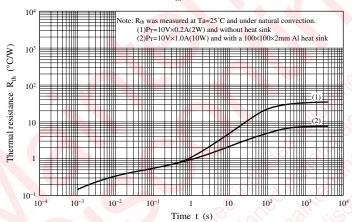
Safe operation area (Reverse bias)



Safe operation area (Reverse bias) measurement circuit







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